DATA SHEET

NEC

# MOS FIELD EFFECT TRANSISTOR
# NP160N04TDG

## SWITCHING
## N-CHANNEL POWER MOS FET

### DESCRIPTION

The NP160N04TDG is N-channel MOS Field Effect Transistor designed for high current switching applications.

### ORDERING INFORMATION

| PART NUMBER | LEAD PLATING | PACKING | PACKAGE |
|---|---|---|---|
| NP160N04TDG-E1-AY Note | Pure Sn (Tin) | Tape 800 p/reel | TO-263-7pin (MP-25ZT) typ. 1.5 g |
| NP160N04TDG-E2-AY Note | | | |

**Note** Pb-free (This product does not contain Pb in the external electrode).

### FEATURES

- Super low on-state resistance
  $R_{DS(on)1}$ = 1.6 mΩ TYP. / 2.0 mΩ MAX. ($V_{GS}$ = 10 V, $I_D$ = 80 A)
  $R_{DS(on)2}$ = 2.2 mΩ TYP. / 5.4 mΩ MAX. ($V_{GS}$ = 4.5 V, $I_D$ = 80 A)
- High Current Rating
  $I_{D(DC)}$ = ±160 A
- Logic level drive type

(TO-263-7pin)


### ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25°C)

| | | | |
|---|---|---|---|
| Drain to Source Voltage ($V_{GS}$ = 0 V) | $V_{DSS}$ | 40 | V |
| Gate to Source Voltage ($V_{DS}$ = 0 V) | $V_{GSS}$ | ±20 | V |
| Drain Current (DC) ($T_C$ = 25°C) | $I_{D(DC)}$ | ±160 | A |
| Drain Current (pulse) Note1 | $I_{D(pulse)}$ | ±640 | A |
| Total Power Dissipation ($T_C$ = 25°C) | $P_{T1}$ | 220 | W |
| Total Power Dissipation ($T_A$ = 25°C) | $P_{T2}$ | 1.8 | W |
| Channel Temperature | $T_{ch}$ | 175 | °C |
| Storage Temperature | $T_{stg}$ | –55 to +175 | °C |
| Single Avalanche Energy Note2 | $E_{AS}$ | 372 | mJ |
| Repetitive Avalanche Current Note3 | $I_{AR}$ | 61 | A |
| Repetitive Avalanche Energy Note3 | $E_{AR}$ | 372 | mJ |

**Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%

**2.** Starting $T_{ch}$ = 25°C, $V_{DD}$ = 20 V, $R_G$ = 25 Ω, $V_{GS}$ = 20 → 0 V, L = 100 μH

**3.** $R_G$ = 25 Ω, $T_{ch(peak)}$ ≤ 150°C

### THERMAL RESISTANCE

| | | | |
|---|---|---|---|
| Channel to Case Thermal Resistance | $R_{th(ch-C)}$ | 0.68 | °C/W |
| Channel to Ambient Thermal Resistance | $R_{th(ch-A)}$ | 83.3 | °C/W |

**The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.**
**Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.**

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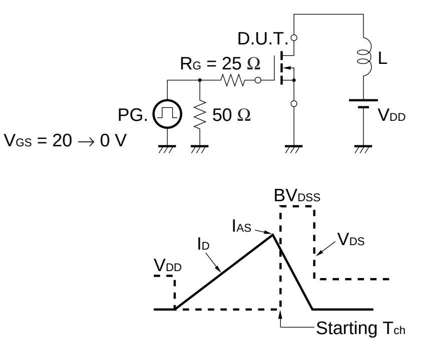
**The mark <R> shows major revised points.**
**The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.**

## ELECTRICAL CHARACTERISTICS ($T_A$ = 25°C)

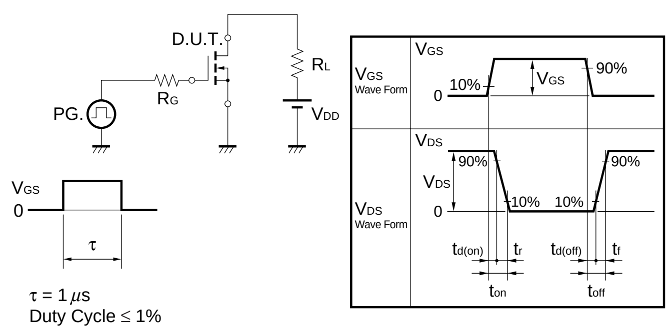
| | CHARACTERISTICS | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|---|
| | Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 40 V, $V_{GS}$ = 0 V | | | 1 | μA |
| | Gate Leakage Current | $I_{GSS}$ | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V | | | ±100 | nA |
| | Gate to Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | 1.5 | 2.0 | 2.5 | V |
| | Forward Transfer Admittance Note | $\mid y_{fs} \mid$ | $V_{DS}$ = 5 V, $I_D$ = 40 A | 37 | 94 | | S |
| | Drain to Source On-state Resistance Note | $R_{DS(on)1}$ | $V_{GS}$ = 10 V, $I_D$ = 80 A | | 1.6 | 2.0 | mΩ |
| | | $R_{DS(on)2}$ | $V_{GS}$ = 4.5 V, $I_D$ = 80 A | | 2.2 | 5.4 | mΩ |
| <R> | Input Capacitance | $C_{iss}$ | $V_{DS}$ = 25 V, | | 10500 | 15750 | pF |
| <R> | Output Capacitance | $C_{oss}$ | $V_{GS}$ = 0 V, | | 980 | 1470 | pF |
| <R> | Reverse Transfer Capacitance | $C_{rss}$ | f = 1 MHz | | 630 | 1140 | pF |
| | Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$ = 20 V, $I_D$ = 80 A, | | 35 | 80 | ns |
| | Rise Time | $t_r$ | $V_{GS}$ = 10 V, | | 55 | 140 | ns |
| | Turn-off Delay Time | $t_{d(off)}$ | $R_G$ = 0 Ω | | 107 | 220 | ns |
| | Fall Time | $t_f$ | | | 17 | 50 | ns |
| | Total Gate Charge Note | $Q_G$ | $V_{DD}$ = 32 V, | | 180 | 270 | nC |
| | Gate to Source Charge | $Q_{GS}$ | $V_{GS}$ = 10 V, | | 30 | | nC |
| | Gate to Drain Charge | $Q_{GD}$ | $I_D$ = 160 A | | 57 | | nC |
| | Body Diode Forward Voltage Note | $V_{F(S-D)}$ | $I_F$ = 160 A, $V_{GS}$ = 0 V | | 0.9 | 1.5 | V |
| | Reverse Recovery Time | $t_{rr}$ | $I_F$ = 160 A, $V_{GS}$ = 0 V, | | 49 | | ns |
| | Reverse Recovery Charge | $Q_{rr}$ | di/dt = 100 A/μs | | 60 | | nC |

**Note** Pulsed test

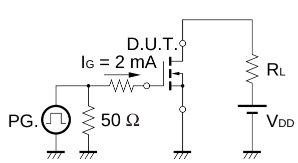
### TEST CIRCUIT 1 AVALANCHE CAPABILITY




### TEST CIRCUIT 2 SWITCHING TIME

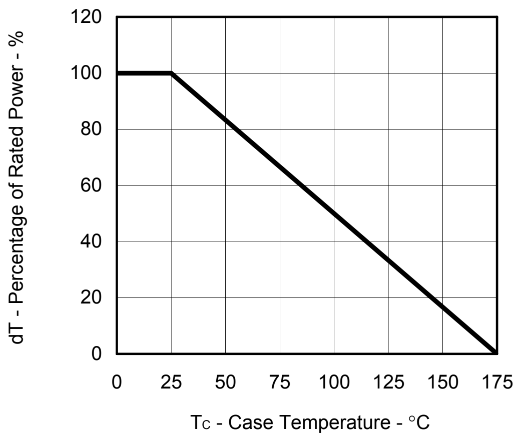



### TEST CIRCUIT 3 GATE CHARGE

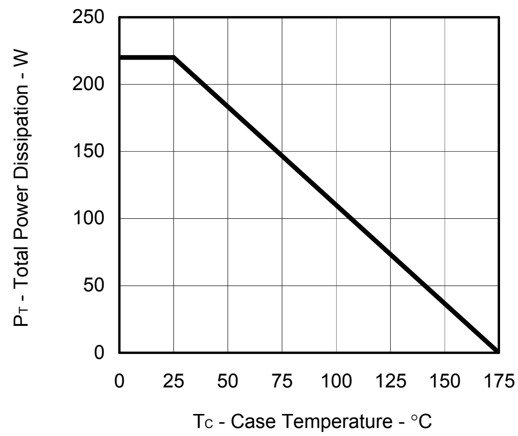


## TYPICAL CHARACTERISTICS ($T_A$ = 25°C)

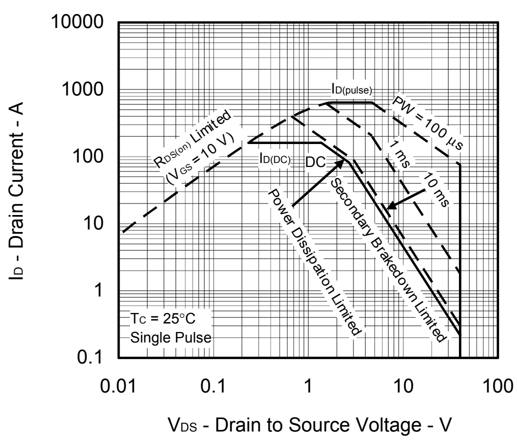
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



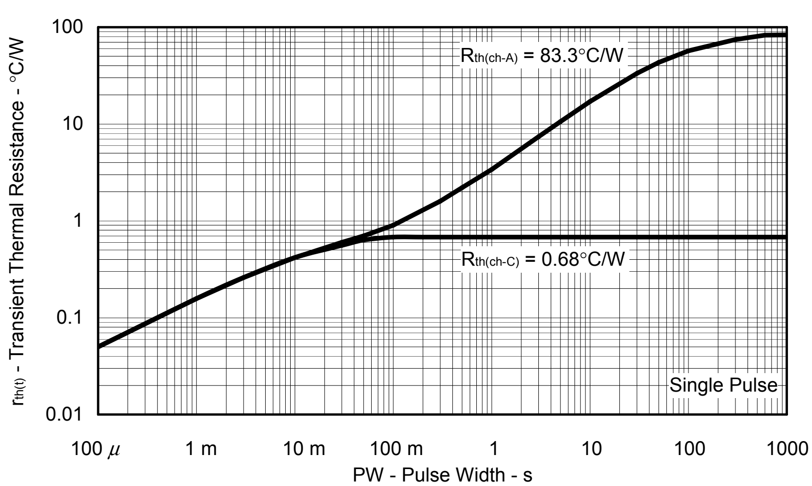

TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



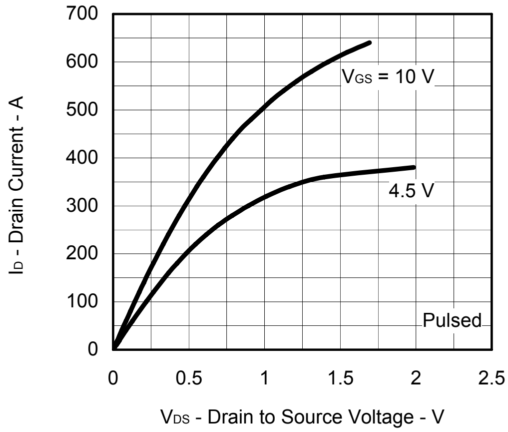

FORWARD BIAS SAFE OPERATING AREA



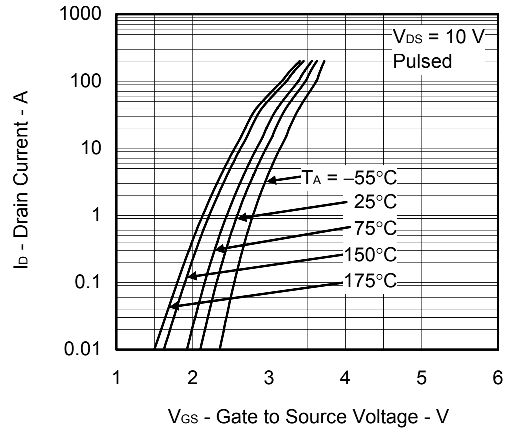

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



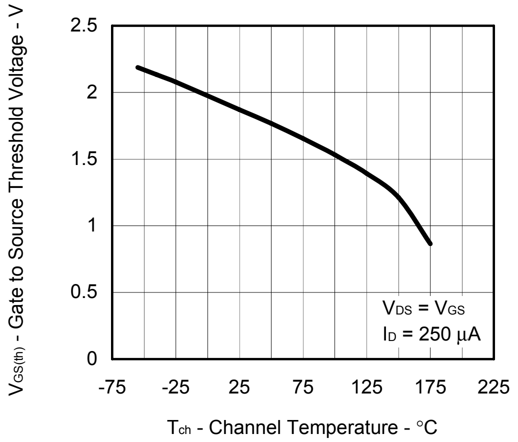
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



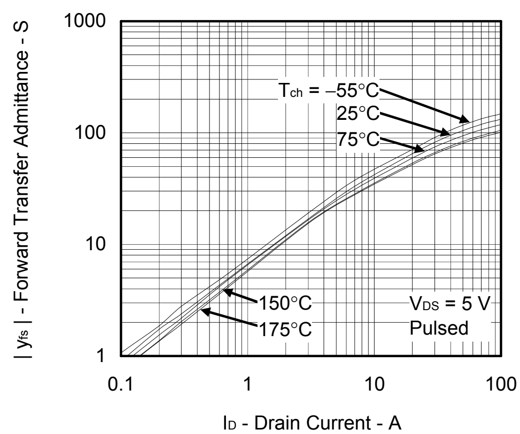

FORWARD TRANSFER CHARACTERISTICS



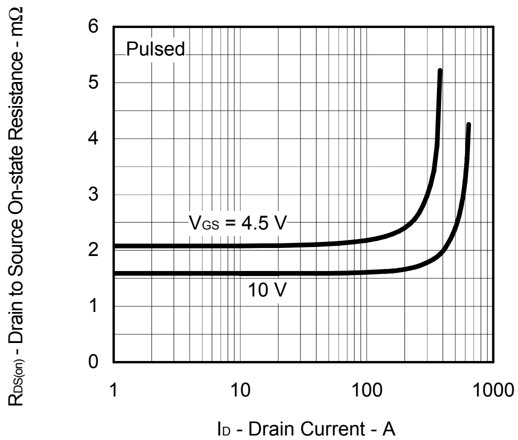

GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATURE



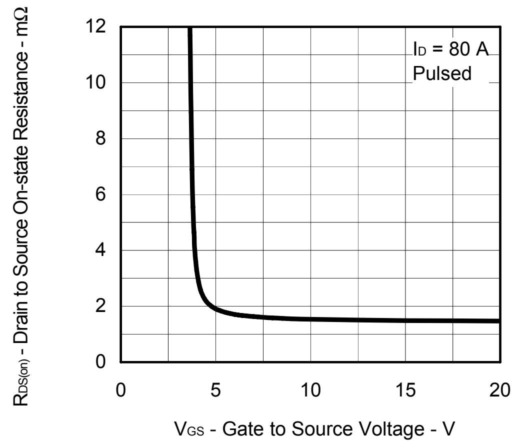

FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



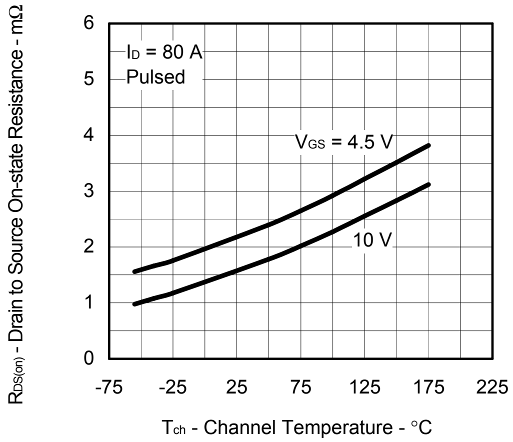

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



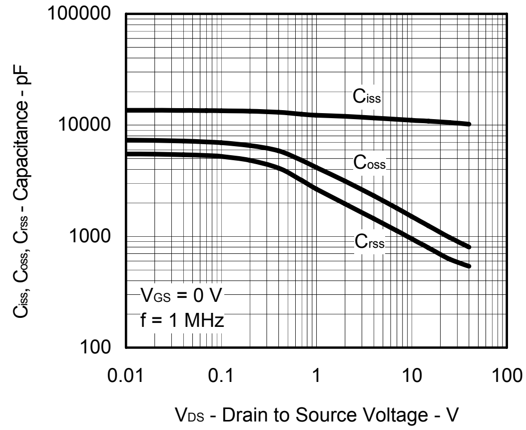

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



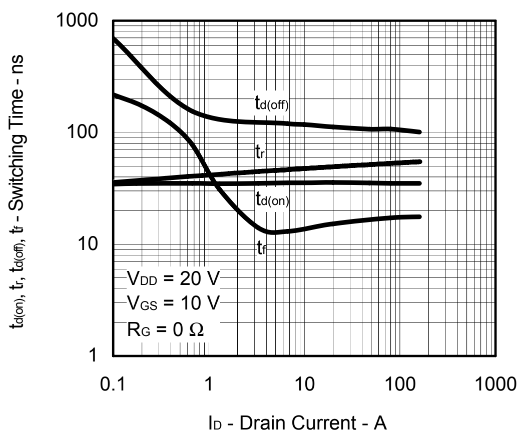
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
CHANNEL TEMPERATURE



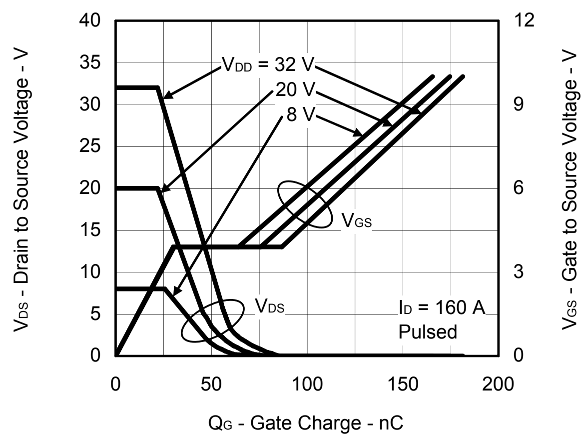

<R> CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



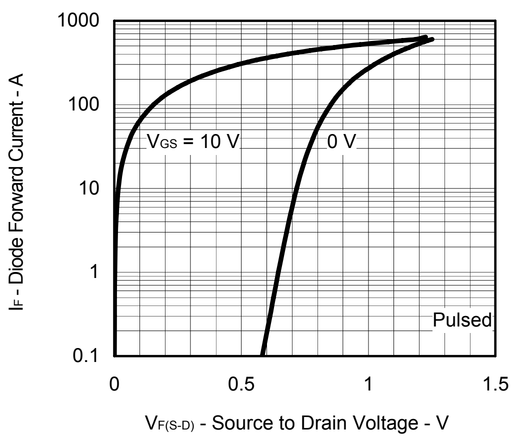

SWITCHING CHARACTERISTICS



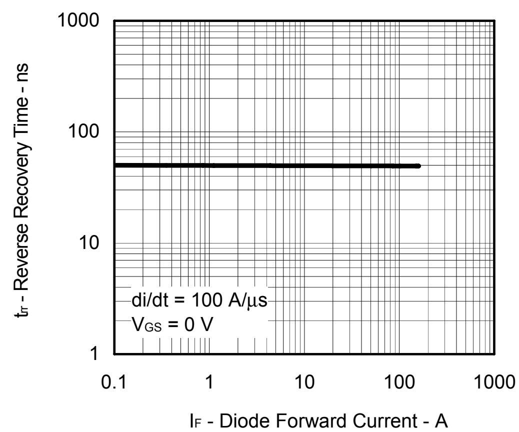

DYNAMIC INPUT/OUTPUT CHARACTERISTICS




SOURCE TO DRAIN DIODE
FORWARD VOLTAGE

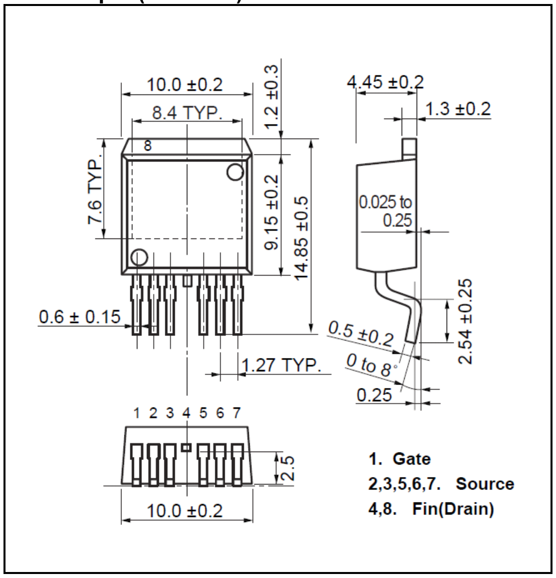



REVERSE RECOVERY TIME vs.
DIODE FORWARD CURRENT

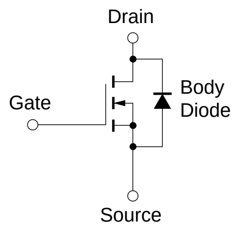


## PACKAGE DRAWING (Unit: mm)

**TO-263-7pin (MP-25ZT)**



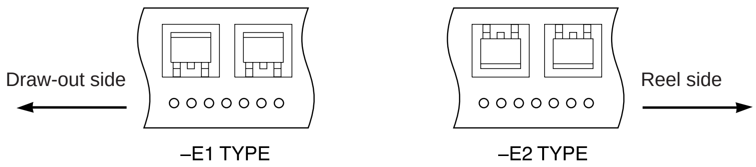

## EQUIVALENT CIRCUIT



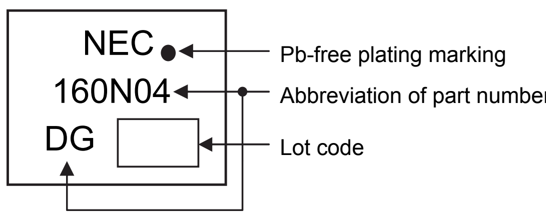

**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

## TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.




## MARKING INFORMATION




## RECOMMENDED SOLDERING CONDITIONS

The NP160N04TDG should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

| Soldering Method | Soldering Conditions | Recommended Condition Symbol |
|---|---|---|
| Infrared reflow | Maximum temperature (Package's surface temperature): 260°C or below<br>Time at maximum temperature: 10 seconds or less<br>Time of temperature higher than 220°C: 60 seconds or less<br>Preheating time at 160 to 180°C: 60 to 120 seconds<br>Maximum number of reflow processes: 3 times<br>Maximum chlorine content of rosin flux (percentage mass): 0.2% or less | IR60-00-3 |
| Partial heating | Maximum temperature (Pin temperature): 350°C or below<br>Time (per side of the device): 3 seconds or less<br>Maximum chlorine content of rosin flux: 0.2% (wt.) or less | P350 |

**Caution Do not use different soldering methods together (except for partial heating).**